

Solid State Devices, Inc.

14701 Firestone Blvd * La Mirada, ČA 90638 Phone: (562) 404-4474 * Fax: (562) 404-1773 ssdi@ssdi-power.com * www.ssdi-power.com

Designer's Data Sheet

Part Number/Ordering Information ^{1/} SFS302 ____ S.22 ___

Screening ^{2/}
= Not Screened

TX = TX Level TXV = TXV S = S Level

Voltage/Family

7 = 30V

8 = 60V

9 = 100V

SFS3027S.22 through SFS3029S.22

0.5 AMP, 30 - 100 Volt SILICON CONTROLLED RECTIFIER

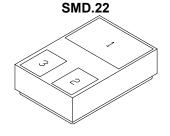
FEATURES:

- Passivated planar construction
- Low on-state voltage and fast switching
- Hermetically Sealed surface mount power package

MAXIMUM RATINGS		Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage	SFS3027 SFS3028 SFS3029	$oldsymbol{V}_{DRM}$	30 60 100	Volts
Non-Repetitive Peak Reverse Blocking Voltage (t < 5.0 ms)	SFS3027 SFS3028 SFS3029	V_{RSM}	50 100 200	Volts
RMS On-State Current, (All Conduction Angles, T _C = 100°C)		I _{T (RMS)}	0.5	Amps
Peak Non-Repetitive Surge Current (One Cycle, 60 Hz)		I _{TSM}	8	Amps
Peak Gate Power		P_{GM}	0.1	Watts
Average Gate Current		I _{G(ave)}	0.025	Amps
Peak Gate Current		I _{GM}	0.25	Amps
Reverse Gate Current		I_{GR}	0.003	Amps
Reverse Gate Voltage		V_{GM}	5.0	Volts
Operating Junction Temperature Range		TJ	-65 to +150	°C
Storage Temperature Range		T _{stg}	-65 to +200	°C
Thermal Resistance, Junction to Case		$R_{ heta JC}$	15	°C/W

NOTES:

- 1/ For ordering information, price, operating curves, and availability- Contact factory.
- 2/ Screening based on MIL-PRF-19500. Screening flows available on request.
- 3/ Unless otherwise specified, all electrical characteristics @25°C.



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: SCR010B

DOC



SFS3027S.22 through SFS3029S.22

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ELECTRICAL CHARACTERIST	ics	Symbol	Min	Typical	Max	Unit
Peak Reverse Blocking Current Rated V_{RRM} , R_{GK} = 1000 Ω	$T_C = 25$ °C $T_C = 150$ °C	I _{RRM}	_	0.08 0.15	0.1 50	μΑ
Peak Forward Blocking Current Rated V_{DRM} , R_{GK} = 1000 Ω	$T_C = 25$ °C $T_C = 150$ °C	I _{DRM}	_	0.08 0.15	0.1 20	μΑ
Peak On-State Voltage I _F = 1.0 A pulse		V_{TM}	0.8	1.1	1.5	٧
Gate Trigger Current $V_D = 5 V_{DC}, R_L = 100 \Omega, R_e = 10 k\Omega$	$T_C = 25$ °C $T_C = -65$ °C	I _{GT}	_ _	25 50	200 1200	μΑ
Gate Trigger Voltage $V_D = 5 V_{DC}, R_L = 100 \Omega, R_e = 100 \Omega$	$T_C = 25$ °C $T_C = -65$ °C $T_C = 150$ °C	V_{GT}	0.4 0.6 0.1	0.55 0.75 0.20	0.8 1.1 0.6	V
Holding Current $V_D = 5 V_{DC}, R_{GK} = 1000 \Omega$	$T_{C} = 25^{\circ}C$ $T_{C} = -65^{\circ}C$ $T_{C} = 150^{\circ}C$	l _Η	0.3 0.5 0.05	1.0 1.5 0.38	5.0 10.0 1.0	mA

